SK25MLI065



IGBT Module

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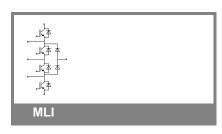
Target Data

Features

- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultra Fast NPT IGBT technology
- CAL technology FWD

Typical Applications*

Multi level inverter



Absolute Maximum Ratings $T_s = 25 ^{\circ}\text{C}$, unless otherwise specified						
Symbol	Conditions		Values	Units		
IGBT			•			
V_{CES}	T _j = 25 °C		600	V		
I _C	T _j = 125 °C	T _s = 25 °C	30	Α		
		T _s = 80 °C	22	Α		
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		60	Α		
V_{GES}			± 20	V		
t _{psc}	V_{CC} = 300 V; $V_{GE} \le 20$ V; $V_{CES} < 600$ V	T _j = 125 °C	10	μs		
Inverse I	Diode					
I _F	T _j = 150 °C	$T_s = 25 ^{\circ}C$	36	Α		
		T _s = 80 °C	24	Α		
I _{FRM}	I _{FRM} = 2 x I _{Fnom}			Α		
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C	200	Α		
Freewhe	eling Diode					
I _F	T _j = 150 °C	T_{case} = 25 °C	36	Α		
		T _{case} = 80 °C	24	Α		
I _{FRM}				Α		
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C	200	Α		
Module						
$I_{t(RMS)}$				Α		
T_{vj}			-40 + 150	°C		
T _{stg}			-40 +12 5	°C		
V _{isol}	AC, 1 min.		2500	V		

Characteristics T _s = 25 °C, unless otherwise specifie						ecified
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.7 \text{ mA}$		3	4	5	V
I _{CES}	$V_{GE} = 0 V, V_{CE} = V_{CES}$	T _j = 25 °C			0,0022	mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C			120	nA
V_{CE0}		T _j = 25 °C		1,4	1,9	V
		T _j = 125 °C		1,7	2,2	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C				mΩ
		T _j = 125°C		44		$m\Omega$
V _{CE(sat)}	I _{Cnom} = 30 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		1,8		V
		T _j = 125°C _{chiplev} .		2,1		V
C _{ies}				1,6		nF
C _{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		0,15		nF
C _{res}				0,09		nF
t _{d(on)}				30		ns
t _r	$R_{Gon} = 33 \Omega$	$V_{CC} = 300V$		25		ns
E _{on}		I _C = 25A		0,75		mJ
^t d(off)	$R_{Goff} = 33 \Omega$	T _j = 125 °C		250		ns
t _f		V _{GE} =±15V		15		ns
E _{off}				0,6		mJ
$R_{th(j-s)}$	per IGBT				1,4	K/W

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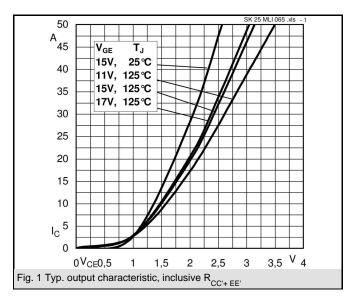
Multi level inverter

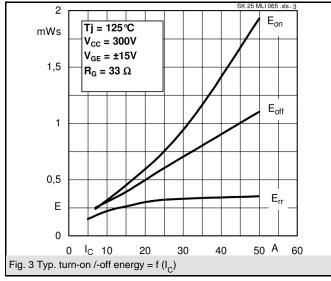
Characteristics								
Symbol	Conditions		min.	typ.	max.	Units		
Antiparallel Diode (D1)								
$V_F = V_{EC}$	I_{Fnom} = 25 A; V_{GE} = 0 V	$T_j = 25 ^{\circ}C_{chiplev.}$		1,45		V		
		$T_j = 125 ^{\circ}C_{\text{chiplev.}}$		1,4		V		
V_{F0}		T _j = 25 °C				V		
		T _j = 125 °C		0,85		V		
r _F		T _j = 25 °C				mΩ		
		T _j = 125 °C		22		mΩ		
I _{RRM}	I _F = 25 A	T _j = 125 °C				Α		
Q _{rr}	di/dt = -2400 A/µs					μC		
E _{rr}	V _R = 300V			0,32		mJ		
$R_{\text{th(j-s)D}}$	per diode				1,7	K/W		
	Freewheeling Diode (D2)							
$V_F = V_{EC}$	$I_{Fnom} = 25 \text{ A}; V_{GE} = 0 \text{ V}$			1,45		V		
		$T_j = 125 ^{\circ}C_{\text{chiplev.}}$		1,4		V		
V_{F0}		T _j = 125 °C		0,85		V		
r _F		T _j = 125 °C		22		V		
I _{RRM}	I _F = 25 A	T _j = 125 °C				Α		
Q_{rr}	di/dt = -2400 A/µs					μC		
E _{rr}	V _R =300V			0,32		mJ		
$R_{th(j-s)FD}$	per diode				1,7	K/W		
M _s	to heat sink		2,25		2,5	Nm		
w				30		g		

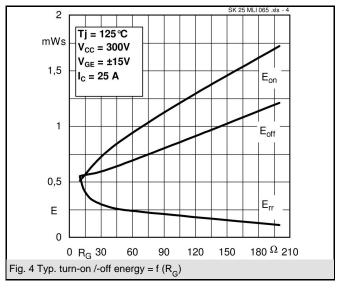
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

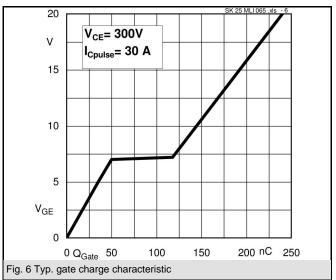
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.











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